

GSM4912

40V N-Channel MOSFETs

Product Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

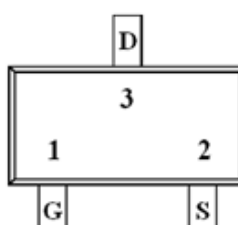
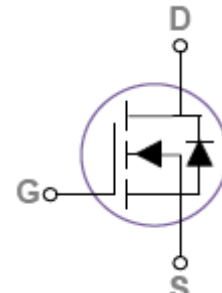
Features

- 40V, 5A, $R_{DS(ON)}=33m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

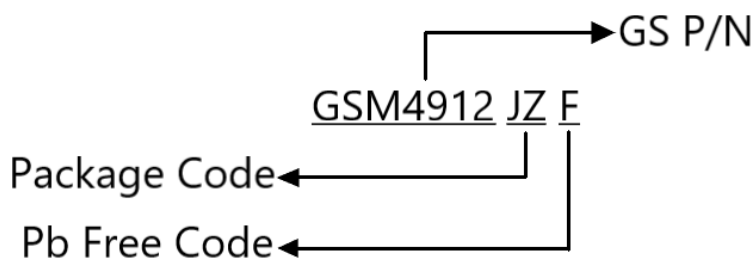
Applications

- MB / VGA / Vcore
- Load Switch
- Hand-Held instrument

Packages & Pin Assignments

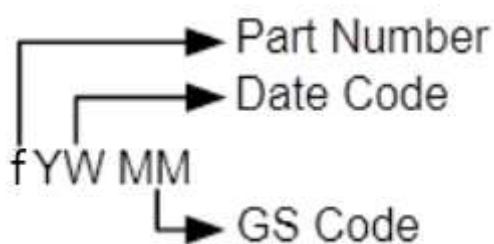
GSM4912JZF (SOT-23)	
 <p>Top Views</p>	
	
Pin	Description
1	Gate
2	Source
3	Drain

Ordering Information



Part Number	Package	Quantity
GSM4912JZF	SOT-23	3000pcs

Marking Information



Part Number	Part Marking	Quantity
GSM4912JZF	fYWMM	3000pcs

Absolute Maximum Ratings

$T_C=25^\circ\text{C}$ Unless otherwise noted

Symbol	Parameter	Typical	Unit
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	5
		$T_C=100^\circ\text{C}$	3
I_{DM}	Pulsed Drain Current ¹	20	A
P_D	Power Dissipation ($T_C=25^\circ\text{C}$)	1.56	W
	Power Dissipation (Derate above 25°C)	0.012	W/ $^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	80	$^\circ\text{C}/\text{W}$

Electrical Characteristics

T_J=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40			V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA		0.04		V/°C
V _{GS(th)}	Gate Threshold Voltage		1.2	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient	V _{DS} =V _{GS} , I _D =250uA		-4		mV/°C
I _{GSS}	Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =40V, V _{GS} =0V			1	uA
		V _{DS} =32V, V _{GS} =0V, T _J =125°C			10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			5	A
I _{SM}	Pulsed Source Current				10	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V, I _D =2A		26	33	mΩ
		V _{GS} =4.5V, I _D =1.5A		33	45	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =4A		6		S
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A			1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =1A,		20		ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/us		7.5		nC
Dynamic						
Q _g	Total Gate Charge ^{2,3}	V _{DS} =20V, V _{GS} =4.5V, I _D =3A		4.7	8	nC
Q _{gs}	Gate-Source Charge ^{2,3}			0.45	1	
Q _{gd}	Gate-Drain Charge ^{2,3}			1.65	3.2	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz		420	800	pF
C _{oss}	Output Capacitance			65	120	
C _{rss}	Reverse Transfer Capacitance			40	80	
t _{d(on)}	Turn-On Time ^{2,3}	V _{DD} =20V, I _D =1A, V _{GS} =4.5V, R _G =25Ω		3.2	6	ns
t _r				8.6	16	
t _{d(off)}	Turn-Off Time ^{2,3}			18	36	
t _f				6	12	

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

Typical Performance Characteristics

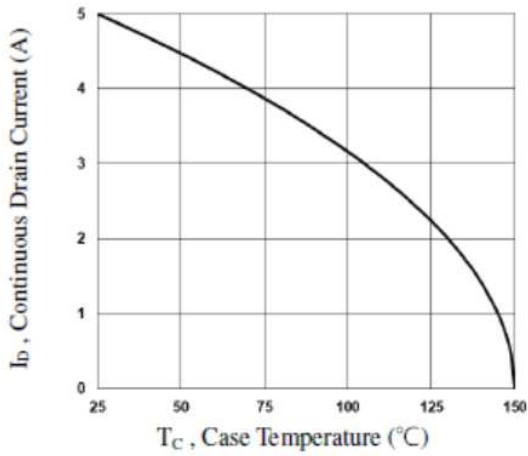


Fig.1 Continuous Drain Current vs. T_c

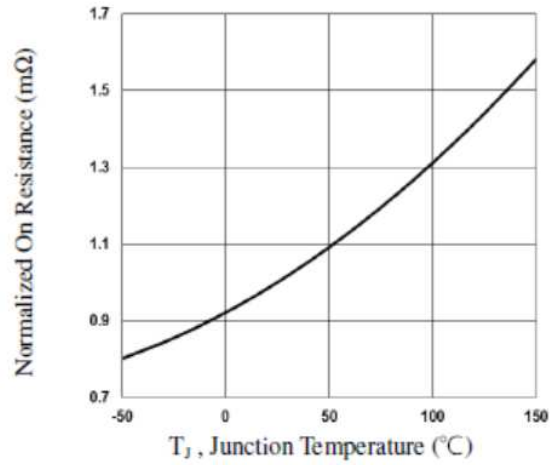


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

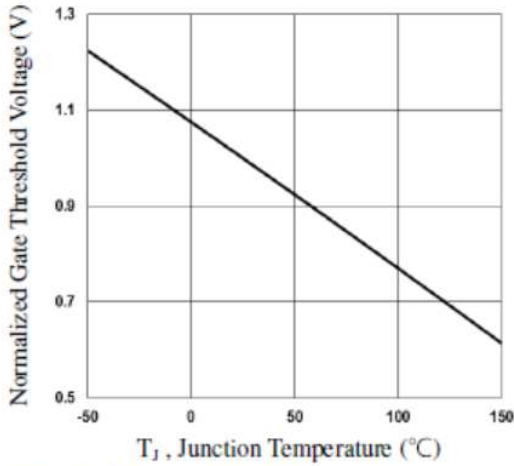


Fig.3 Normalized V_{th} vs. T_j

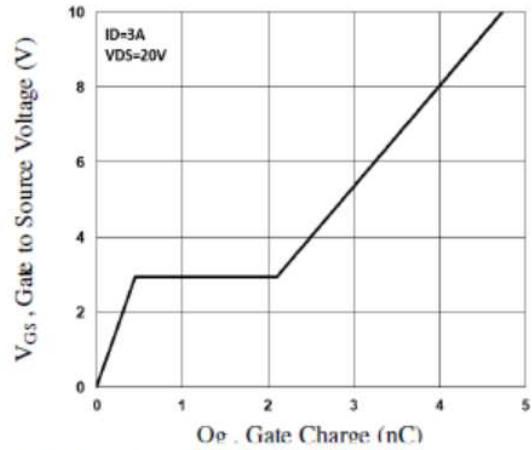


Fig.4 Gate Charge Waveform

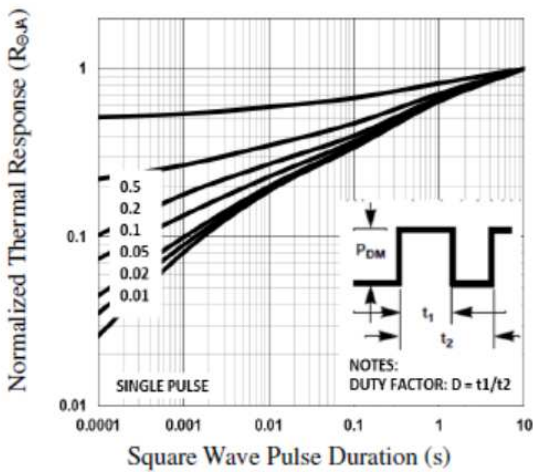


Fig.5 Normalized Transient Response

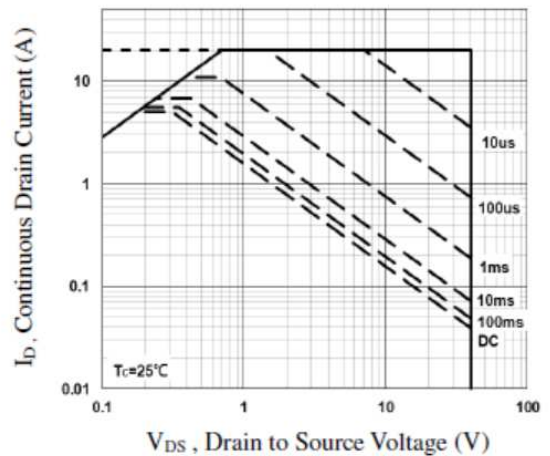


Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics(continue)

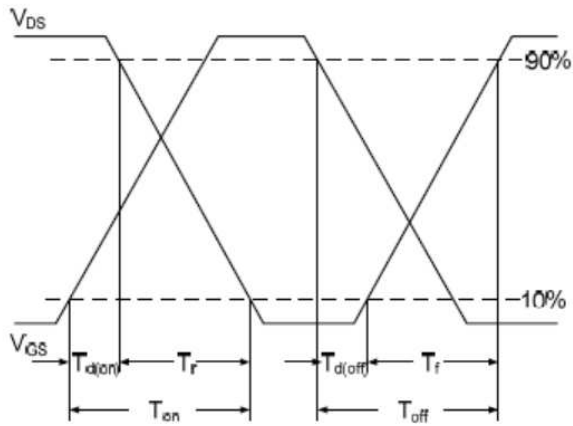


Fig.7 Switching Time Waveform

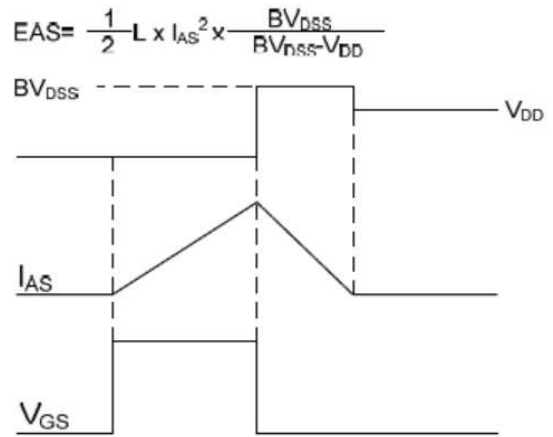
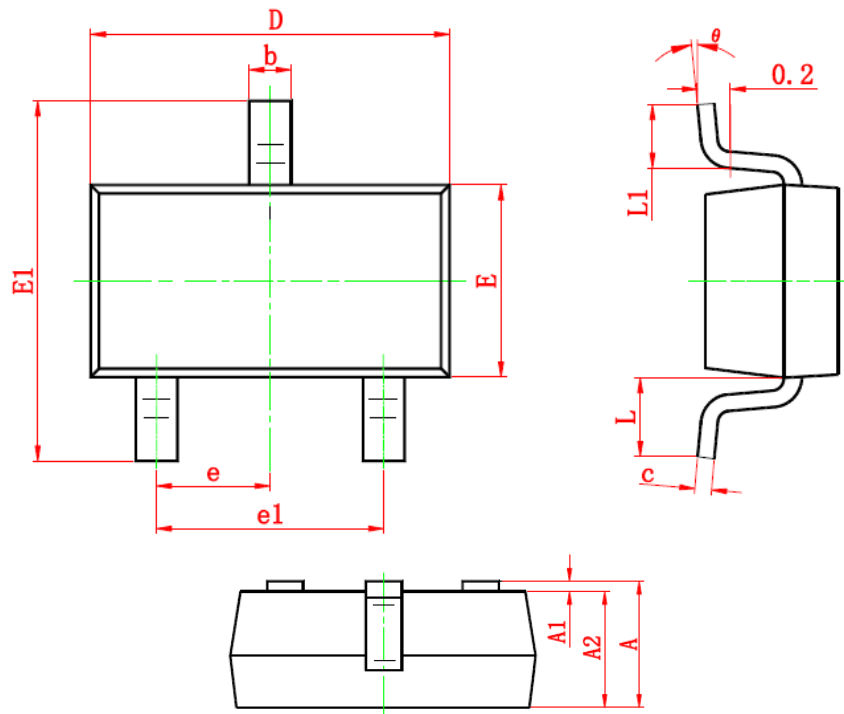


Fig.8 EAS Waveform

Package Dimension

SOT-23







Dimensions



Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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